Description

The DC1271D3 is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The DC1271D3 complies with the IEC61000-4-2(ESD) standard with ±30kV air and ±30kV contact discharge. It is assembled into a SOD-323 lead-free package. The small size and high ESD surge protection make DC1271D3 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one power line or data line
- Ultra low leakage: nA level
- 2-pin leadless package
- Low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test Air discharge: ±30kV
    Contact discharge: ±30kV
  - IEC61000-4-5 (Lightning) 80A (8/20μs)
- RoHS Compliant

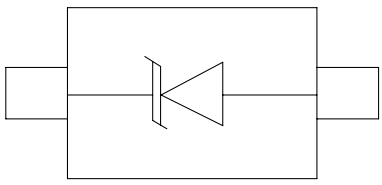
Mechanical Characteristics

- Package: SOD-323
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

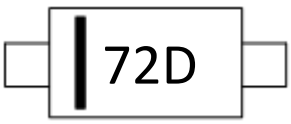
- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks,Desktops,Servers
- Portable Instrumentation
- Laser Diode Protection

Dimensions and Pin Configuration



Circuit and Pin Schematic

Marking Information



72D = Device Marking Code
Bar denotes Cathode

Ordering Information

Part Number	Marking	Packaging	Reel Size
DC1271D3	72D	3000/Tape & Reel	7 inch

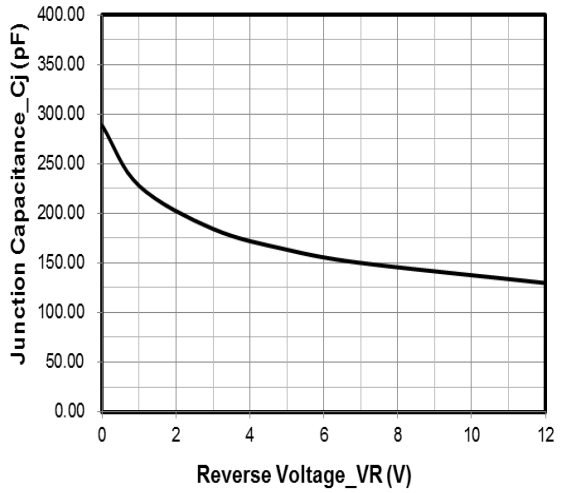
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	2000	W
Peak Pulse Current (8/20μs)	Ipp	80	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±30 ±30	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

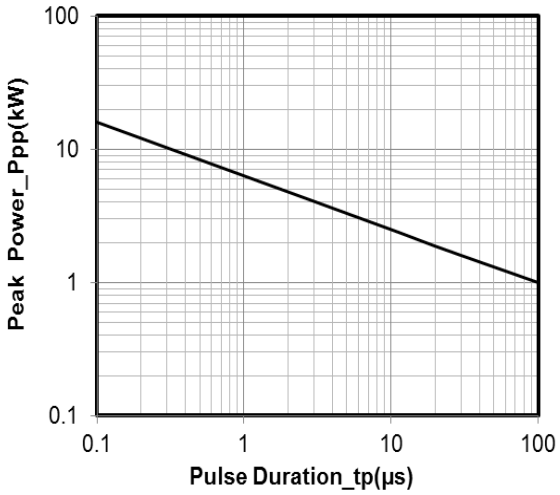
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			12	V	
Breakdown Voltage	V_{BR}	13.3		17.8	V	I_T = 1mA
Reverse Leakage Current	I_R			0.2	μA	V_{RWM} = 12V
Forward Voltage	V_F		1.0	1.2	V	I_F = 10mA
Clamping Voltage	V_C			18	V	I_{PP} = 10A (8 x 20μs pulse)
Clamping Voltage	V_C			25	V	I_{PP} = 80A (8 x 20μs pulse)
Junction Capacitance	C_J			300	pF	VR = 0V, f = 1MHz

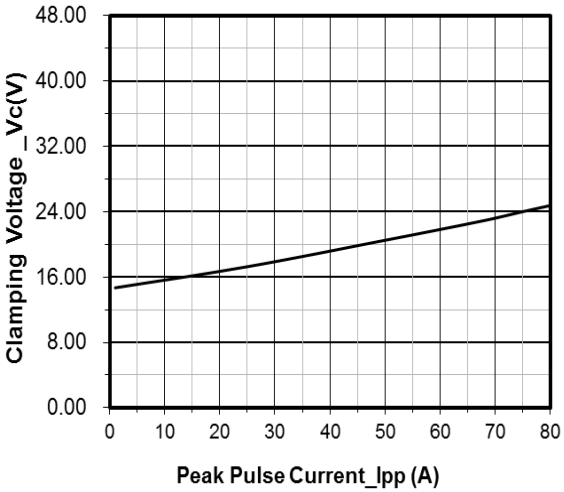
Typical Performance Characteristics (T_A=25℃ unless otherwise Specified)



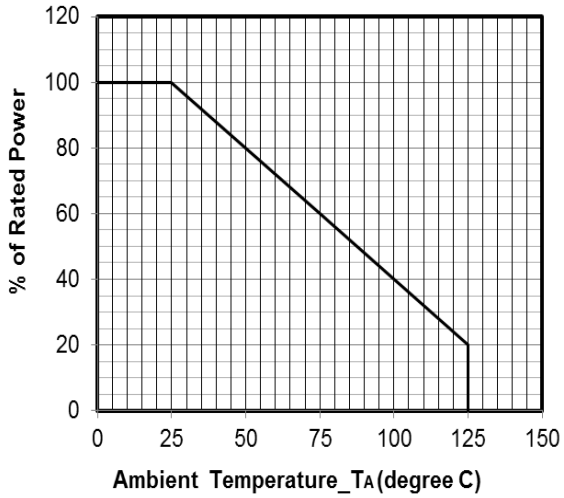
Junction Capacitance vs. Reverse Voltage



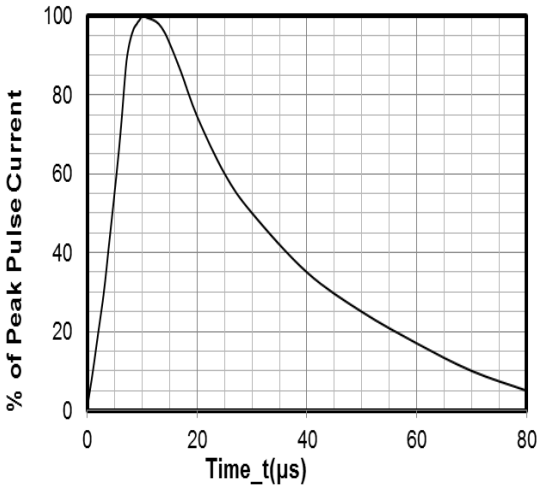
Peak Pulse Power vs. Pulse Time



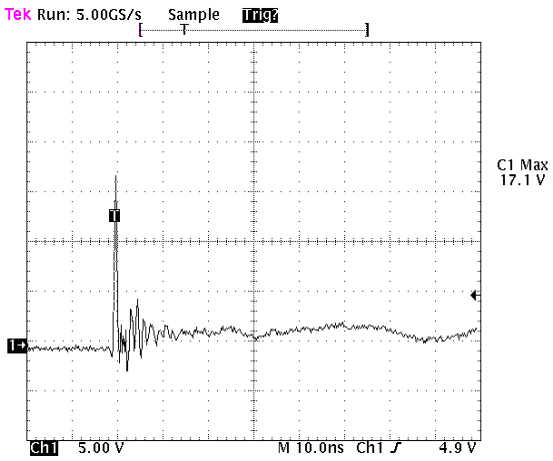
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

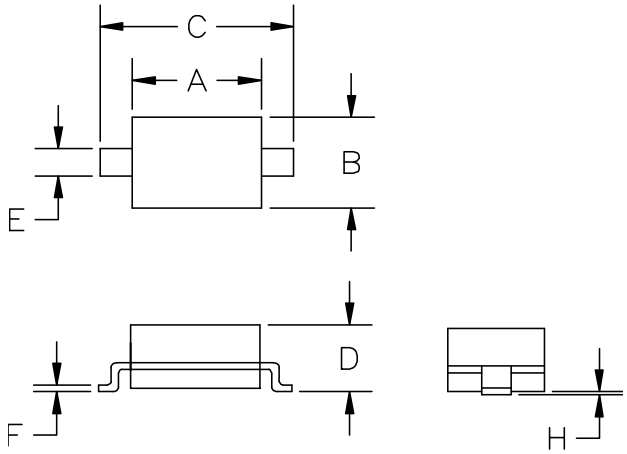


Note：Data is taken with a 10x attenuator

ESD Clamping Voltage

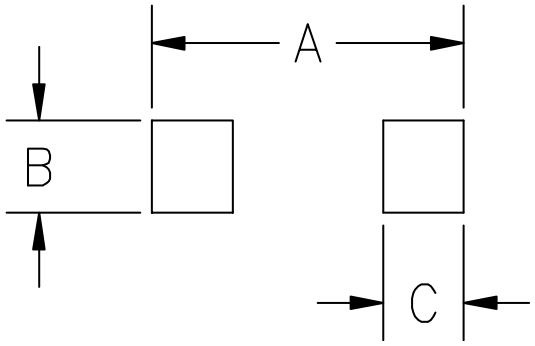
+8 kV Contact per IEC61000−4−2

SOD-323 Package Outline Drawing



SYM	DIMENSIONS			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.50	1.80	0.060	0.071
B	1.20	1.40	0.045	0.054
C	2.30	2.70	0.090	0.107
D	-	1.10	-	0.043
E	0.30	0.40	0.012	0.016
F	0.10	0.25	0.004	0.010
H	-	0.10	-	0.004

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
A	3.15	0.120
B	0.80	0.031
C	0.80	0.031

Contact Information

Changzhou D-first Electronics CO.,Ltd.
www.first-electronic.com
Email: xhf@first-electronic.cn
Phone: +86（0519）88171671